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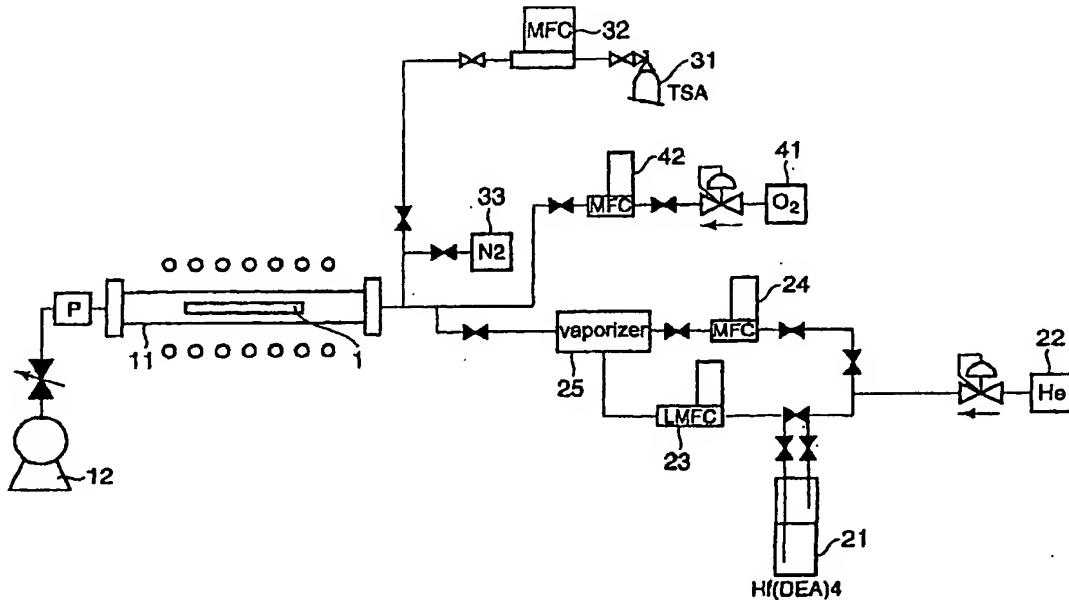
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*[Continued on next page]*

(54) Title: METHOD FOR FORMING DIELECTRIC OR METALLIC FILMS



(57) Abstract: Method for producing a metal silicon (oxy)nitride by introducing a carbon-free silicon source (for example, (SiH<sub>3</sub>)<sub>3</sub>N), a metal precursor with the general formula MX<sub>n</sub> (for example, Hf(NEt<sub>2</sub>)<sub>4</sub>), and an oxidizing agent (for example, O<sub>2</sub>) into a CVD chamber and reacting same at the surface of a substrate. MsIN, MSiO and/or MSiON films may be obtained. These films are useful as high k dielectrics films.

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